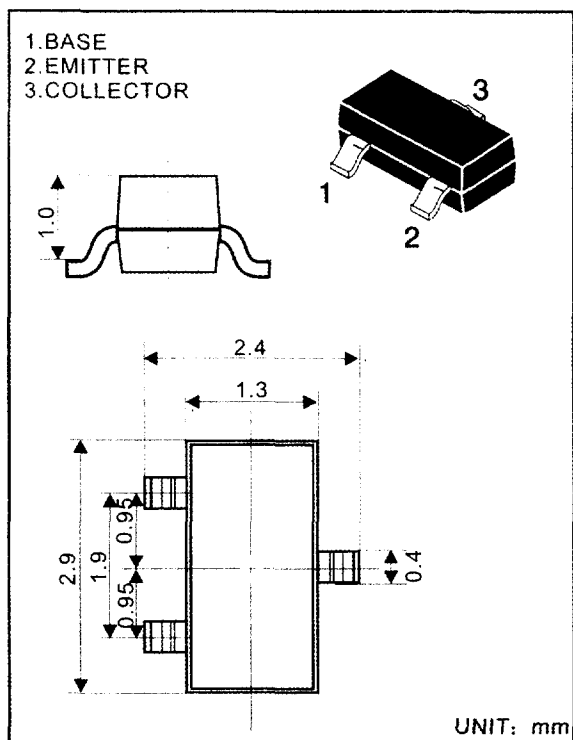


SOT-23 Plastic-Encapsulate Transistors

MMBT3904LT1 TRANSISTOR (NPN)



FEATURES

Power dissipation

P_{CM} : 0.2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.2 A

Collector-base voltage

$V_{(BR)CBO}$: 60V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_C=100\mu A, I_B=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=40V, I_B=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0mA$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=10mA$	100	300	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=50mA$	60		
Collector-emitter saturation voltage	V_{CEsat}	$I_C=100mA, I_B=5mA$		0.4	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=50mA, I_B=5mA$		0.95	
Transition frequency	f_T	$V_{CE}=20V, I_C=10mA, f=100MHz$	250		MHz

DEVICE MARKING : MMBT3904LT1=1AM

Typical Characteristics

MMBT3904LT1

